

S<sub>1</sub>

G<sub>1</sub>

 $S_2$ 

 $G_2$ 

2

3

RoHS

COMPLIANT

HALOGEN

**FREE** Available

Vishay Siliconix

# Dual N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)		
40	0.021 at V <sub>GS</sub> = 10 V	7.4		
	0.028 at V <sub>GS</sub> = 4.5 V	6.4		

8 D<sub>1</sub>

 $D_1$ 

5 D<sub>2</sub>

Si4942DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

7

6 D<sub>2</sub>

SO-8

Top View

Ordering Information: Si4942DY-T1-E3 (Lead (Pb)-free)

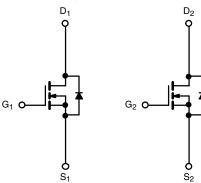
### FEATURES

- Halogen-free According to IEC 61249-2-21
  Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

#### **APPLICATIONS**

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- Low Power Synchronous Rectifier
  - Automotive 12 V Systems



N-Channel MOSFET

N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25 \text{ °C}$ , unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	40		V	
Gate-Source Voltage		V <sub>GS</sub>	± 20			
	T <sub>A</sub> = 25 °C	– I <sub>D</sub>	7.4	5.3		
Continuous Drain Current $(T_J = 150 \ ^{\circ}C)^a$	T <sub>A</sub> = 70 °C		5.8	4.3		
Pulsed Drain Current		I <sub>DM</sub>	30		А	
Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	25			
Continuous Source Current (Diode Conduction) <sup>a</sup>		۱ <sub>S</sub>	1.8	0.9		
	T <sub>A</sub> = 25 °C	– P <sub>D</sub>	2.1	1.1	W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		1.3	0.7	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
	t ≤ 10 s	R <sub>thJA</sub>	50	60	°C/W
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	28	34	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.



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<b>SPECIFICATIONS</b> $T_J = 25 \circ C$	C, unless o	therwise noted					
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{\rm DS} = V_{\rm GS}, I_{\rm D} = 250 \mu {\rm A}$ 1.0 3		3	V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$	± 1		± 100	nA	
Zara Cata Valtaga Drain Current	I <sub>DSS</sub>	$\begin{tabular}{ c c c c c } \hline V_{DS} = 40 \ V, \ V_{GS} = 0 \ V \\ \hline V_{DS} = 40 \ V, \ V_{GS} = 0 \ V, \ T_{J} = 55 \ ^{\circ}C \\ \hline \end{tabular}$			1		
Zero Gate Voltage Drain Current				5	μΑ		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			А	
	D	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 7.4 \text{ A}$ $V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 6.4 \text{ A}$		0.017	0.021	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>			0.023	0.028		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 7.4 A		25		S	
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_{S} = 1.8 \text{ A}, V_{GS} = 0 \text{ V}$		0.75	1.1	V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg			21	32		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ = 20 V, $V_{GS}$ = 10 V, $I_D$ = 5.7 A		3.3		nC	
Gate-Drain Charge	Q <sub>gd</sub>			5.8		1	
Gate Resistance	R <sub>g</sub>		0.5	1.1	1.6	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			13	20		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 20 V, $R_L$ = 20 $\Omega$		10	15		
Turn-Off Delay Time	t <sub>d(off)</sub>	$t_{d(off)}$ I <sub>D</sub> $\cong$ 1 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 6 $\Omega$		31	50	ns	
Fall Time	t <sub>f</sub>			11	20		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	$I_F = 1.8 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		30	60		

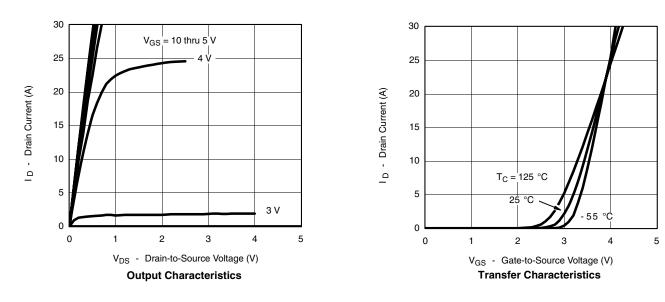
Notes:

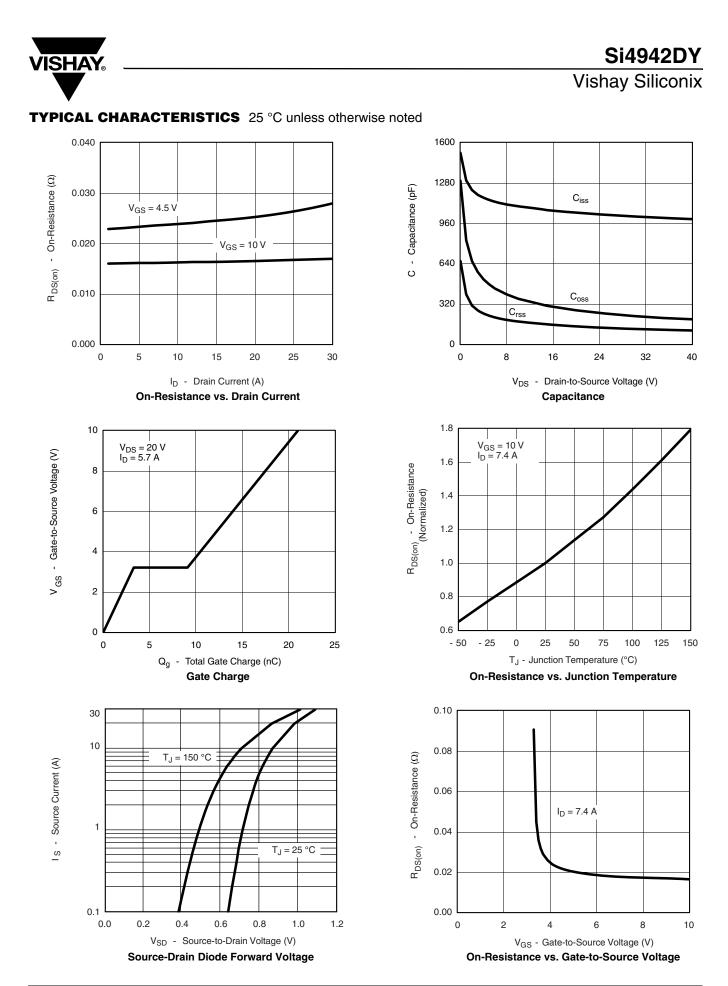
a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

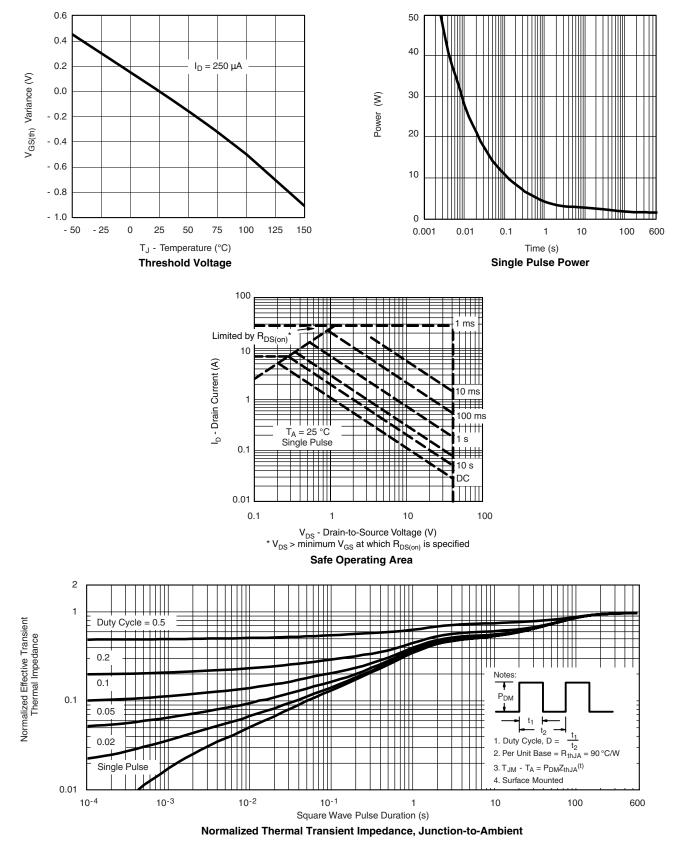
#### TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



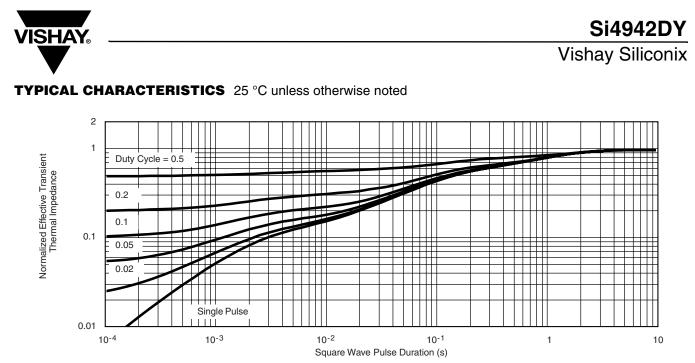


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**/ISHA**`



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?71887">www.vishay.com/ppg?71887</a>.



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